PMPB85ENEA

60 V, single N-channel Trench MOSFET

19 December 2013 **Product data sheet**

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	4.4	A
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 3 A; T_j = 25 °C		-	72	95	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

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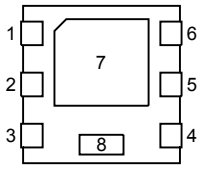
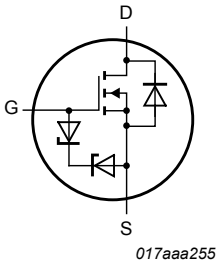
5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	 Transparent top view **DFN2020MD-6 (SOT1220)**	
2	D	drain		
3	G	gate		
4	S	source		
5	D	drain		
6	D	drain		
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMPB85ENEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB85ENEA	2C

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	4.4	A
		V_{GS} = 10 V; T_{amb} = 25 °C	[1]	-	3	A
		V_{GS} = 10 V; T_{amb} = 100 °C	[1]	-	1.9	A
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; t_p ≤ 10 µs		-	12	A

Symbol	Parameter	Conditions		Min	Max	Unit
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.4 A; DUT in avalanche (unclamped)		-	12.6	mJ
P_{tot}	total power dissipation	T_{amb} = 25 °C	[1]	-	1.6	W
		T_{amb} = 25 °C; t ≤ 5 s	[1]	-	3.3	W
		T_{sp} = 25 °C		-	15.6	W
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{amb} = 25 °C	[1]	-	1	A
ESD maximum rating						
V_{ESD}	electrostatic discharge voltage	HBM	[2]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

[2] Measured between all pins.

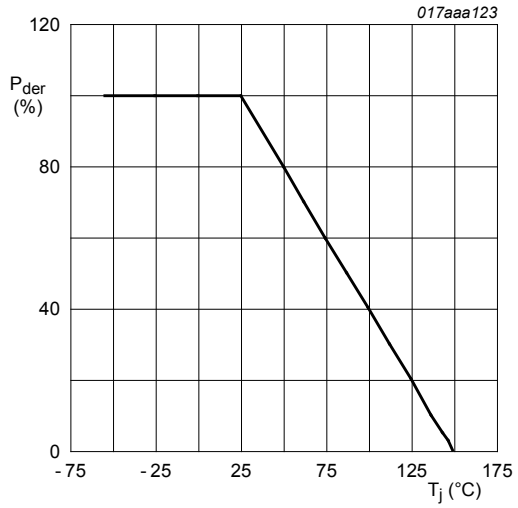


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

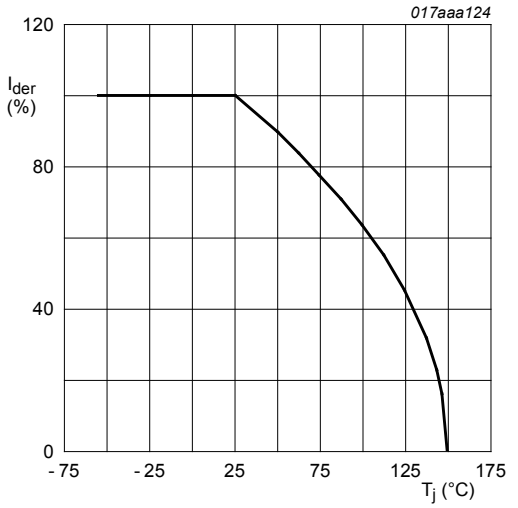
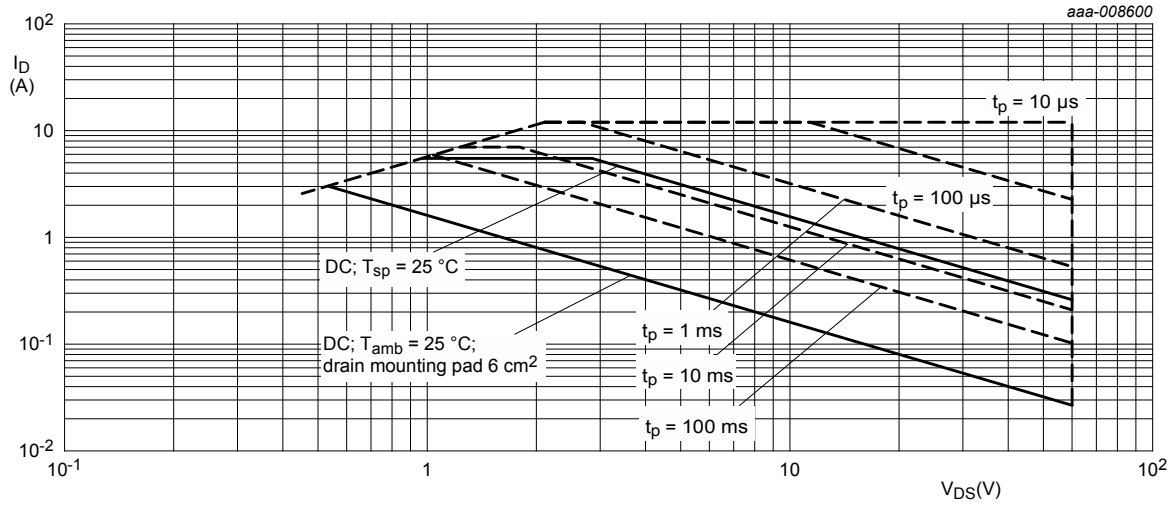


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$



I_{DM} = single pulse

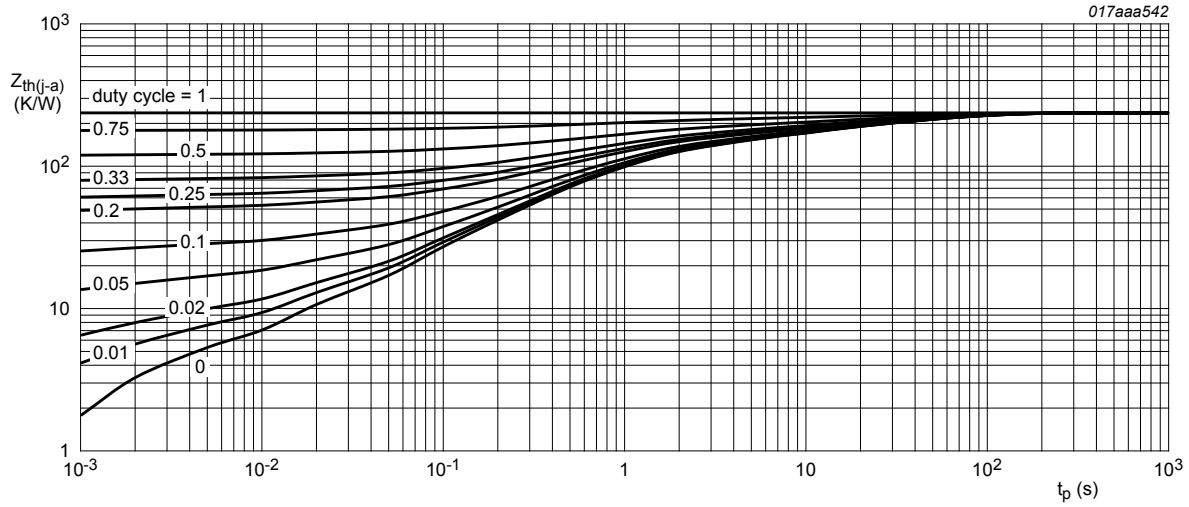
Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

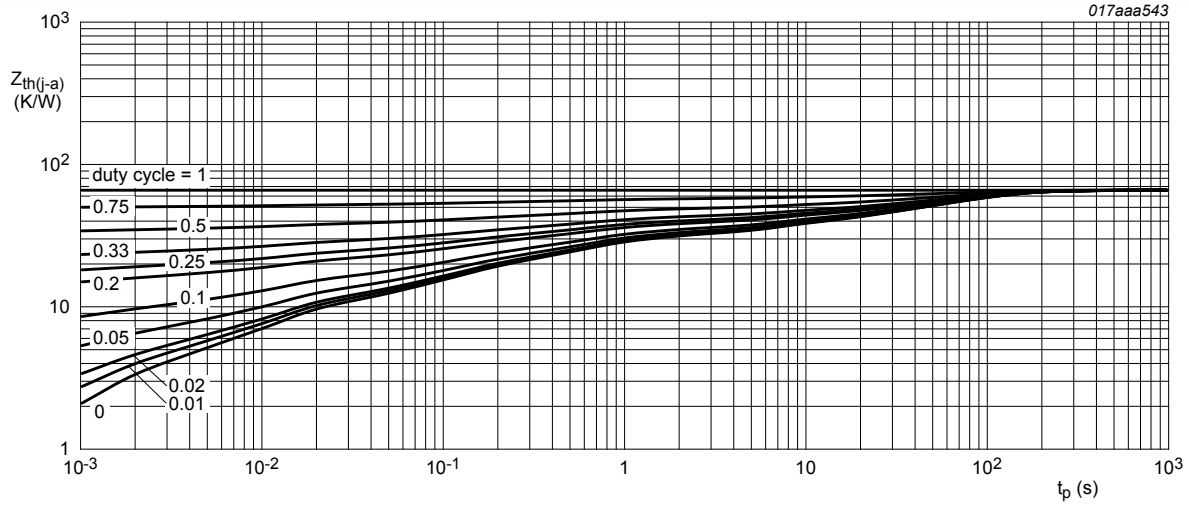
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	239	275	K/W
			[2]	-	68	78	K/W
		in free air; t ≤ 5 s	[2]	-	33	38	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	4	8	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



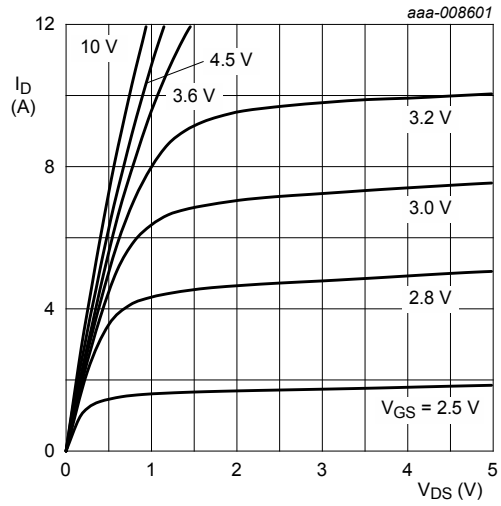
FR4 PCB, mounting pad for drain 6 cm^2

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

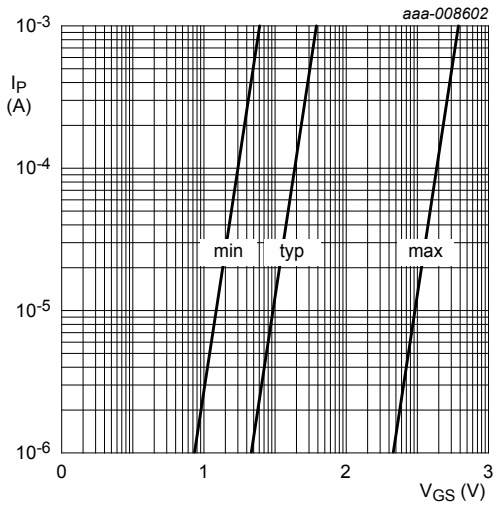
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		60	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS}; T_j = 25 °C		1.3	1.7	2.7	V
I_{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C		-	-	1	µA
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 150 °C		-	-	10	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	10	µA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-10	µA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C		-	-	1	µA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-1	µA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 3 A; T_j = 25 °C		-	72	95	mΩ
		V_{GS} = 10 V; I_D = 3 A; T_j = 150 °C		-	135	175	mΩ
		V_{GS} = 4.5 V; I_D = 2.8 A; T_j = 25 °C		-	85	120	mΩ
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 3 A; T_j = 25 °C		-	11.5	-	S
R_G	gate resistance	f = 1 MHz; T_j = 25 °C		-	1.7	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	V_{DS} = 30 V; I_D = 3 A; V_{GS} = 10 V; T_j = 25 °C		-	6.2	9.2	nC
Q_{GS}	gate-source charge			-	0.8	-	nC
Q_{GD}	gate-drain charge			-	1.2	-	nC
C_{iss}	input capacitance	V_{DS} = 30 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	305	-	pF
C_{oss}	output capacitance			-	40	-	pF
C_{rss}	reverse transfer capacitance			-	25	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; I_D = 3 A; V_{GS} = 10 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C		-	4	-	ns
t_r	rise time			-	3.5	-	ns
$t_{d(off)}$	turn-off delay time			-	10.5	-	ns
t_f	fall time			-	4.5	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 1 A; V_{GS} = 0 V; T_j = 25 °C		-	0.8	1.2	V



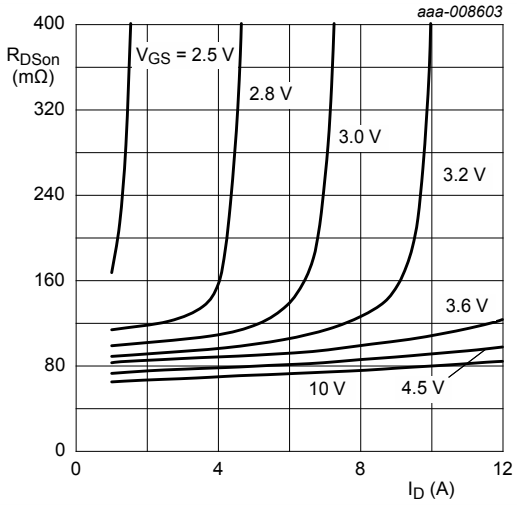
T_j = 25 °C

Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



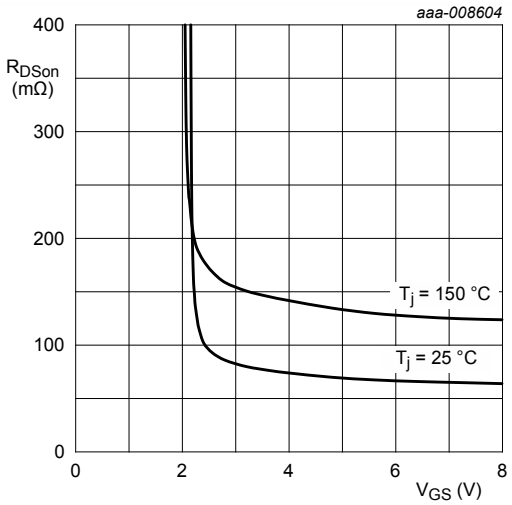
T_j = 25 °C; V_{DS} = 10 V

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



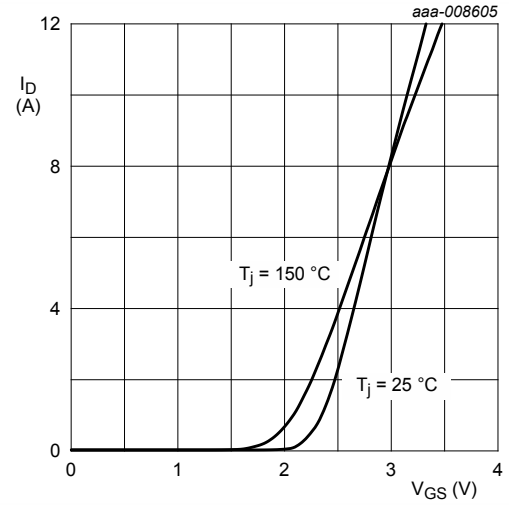
T_j = 25 °C

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



I_D = 2.8 A

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



$V_{DS} > I_D \times R_{DSon}$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

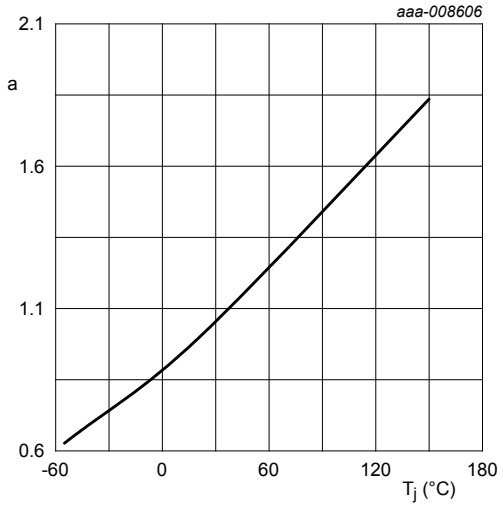
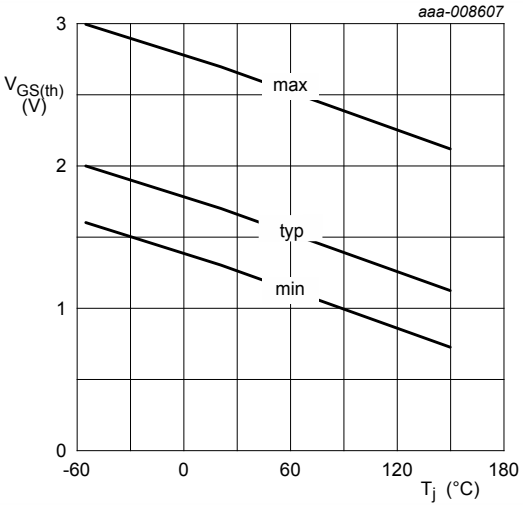


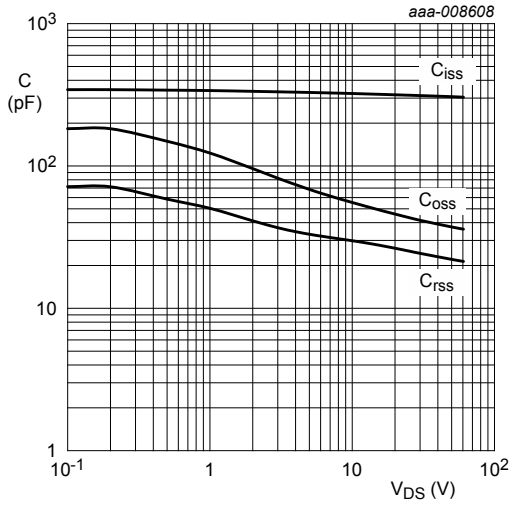
Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$



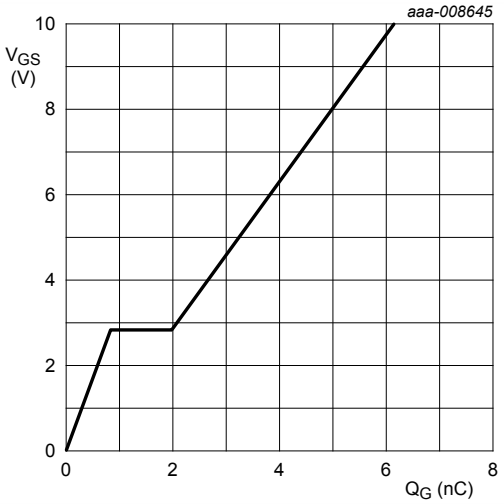
I_D = 0.25 mA; $V_{DS} = V_{GS}$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; V_{GS} = 0 V

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



I_D = 3 A; V_{DS} = 30 V; T_{amb} = 25 °C

Fig. 14. Gate-source voltage as a function of gate charge; typical values

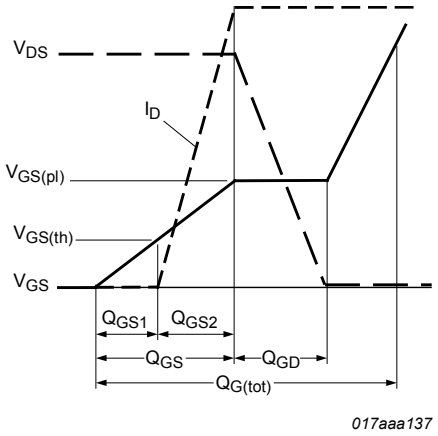
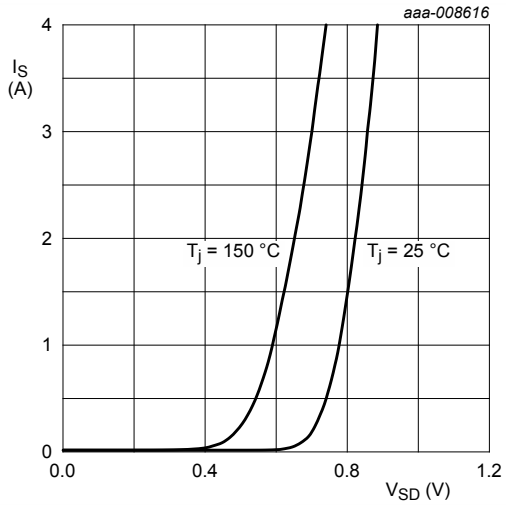


Fig. 15. MOSFET transistor: Gate charge waveform definitions



V_{GS} = 0 V

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

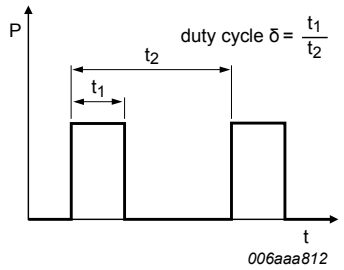


Fig. 17. Duty cycle definition

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

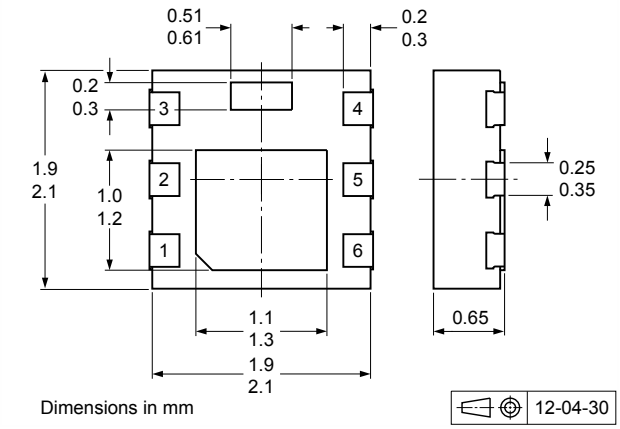


Fig. 18. Package outline DFN2020MD-6 (SOT1220)

13. Soldering

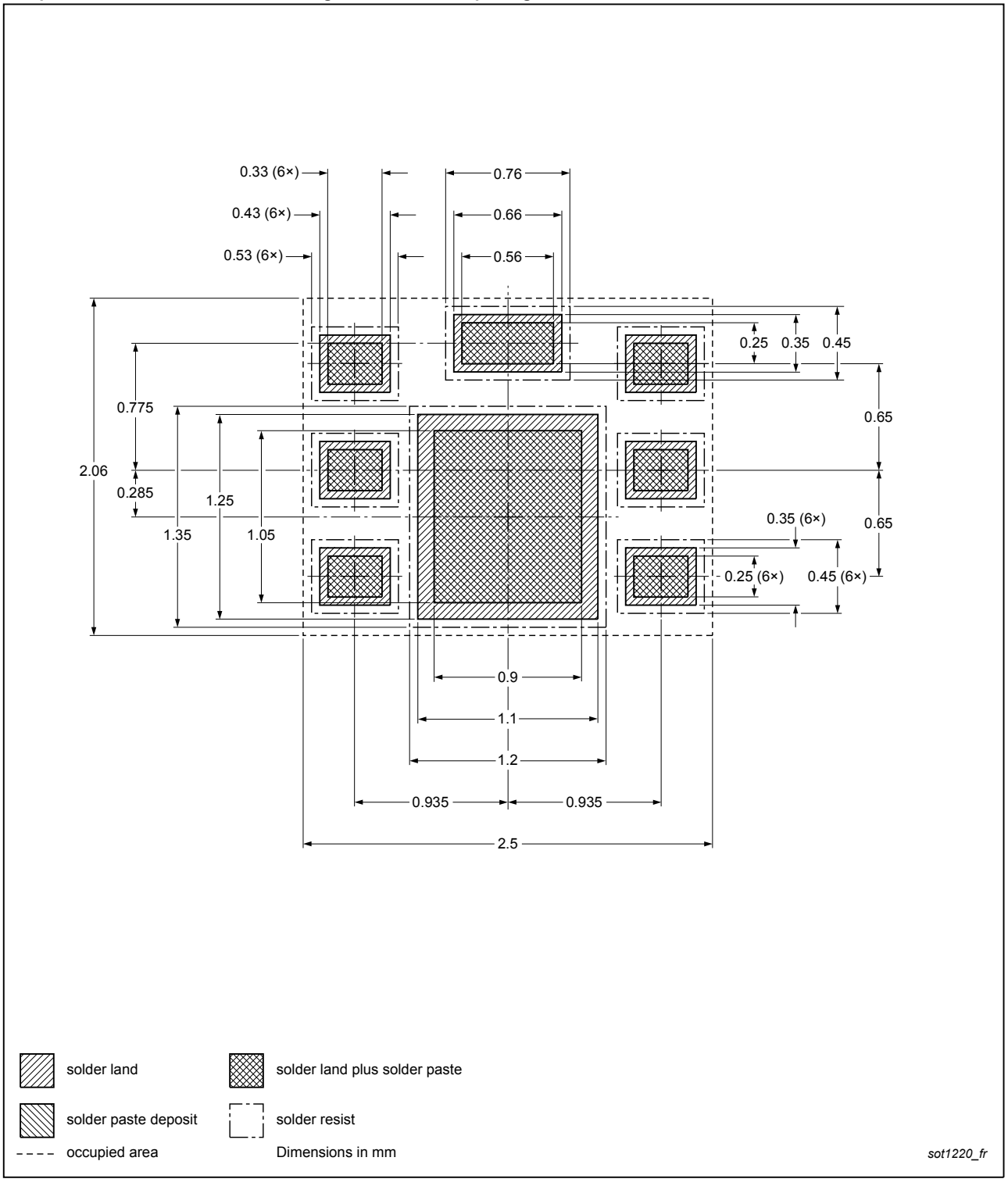


Fig. 19. Reflow soldering footprint for DFN2020MD-6 (SOT1220)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB85ENEA v.2	20131219	Product data sheet	-	PMPB85ENEA v.1
Modifications:	• Products status changed			
PMPB85ENEA v.1	20130219	Objective data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
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16. Contents

1 General description 1
2 Features and benefits 1
3 Applications 1
4 Quick reference data 1
5 Pinning information 2
6 Ordering information 2
7 Marking 2
8 Limiting values 2
9 Thermal characteristics 4
10 Characteristics 6
11 Test information 10
11.1 Quality information 10
12 Package outline 10
13 Soldering 11
14 Revision history 12
15 Legal information 13
15.1 Data sheet status 13
15.2 Definitions 13
15.3 Disclaimers 13
15.4 Trademarks 14

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